

Supporting Information

Multi-Functional interface modulation through thiol functionalized covalent organic frameworks for efficient and durable perovskite solar cells

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Experimental section

Materials

The indium tin oxide (ITO, $15 \Omega \text{ sq}^{-1}$) was provided via Wuhu Jinghui Electronic Technology Co., Ltd); Chlorobenzene (CB, 99.9%), N, N-dimethylformamide (DMF, 99.8%), and isopropanol (IPA, 99.5%) were from Sigma-Aldrich; Dimethyl sulfoxide (DMSO, 99.9%) was from Alfa Aesar; Perovskite precursor reagents, Phenyl-C61-butyric acid methyl ester (PCBM, 99%) and [2-(3,6-Dimethoxy-9H-carbazol-9-yl)ethyl]phosphonic Acid (MeO-2PACz, 99%) were purchased Xi'an Polymer Light Technology Corp., China; Bathocuproine (BCP, >98%), 2,5-diaminobenzene-1,4-dithiol dihydrochloride (99.9%) and 1,3,5-triformylphloroglucinol (99.9%) were obtained from Aladdin Reagent Co., Ltd; All the commercial materials were from commercial channels and used without further treatment.

Preparation of thiol-functionalized COFs

Thiol-functionalized COFs (SH-COF) were synthesized by two kinds of precursors based on the Schiff-base reactions. 1,3,5-triformylphloroglucinol (TFP) (63 mg, 0.3 mmol) and 2,5-diaminobenzene-1,4-dithiol dihydrochloride (DBD) (110 mg, 0.45 mmol) were precisely weighted and added to a 10 mL Schlenk glass reaction tube. Then, 1.5 mL of mesitylene, 1.5 mL of dioxane and 0.5 mL of 3 M acetic acid was transferred into the container. The mixture was ultrasonicated for 30 min in order to uniformly dispersed. After three freeze-thaw degassing treatments in liquid N_2 bath, the tube was heated at $120 \text{ }^\circ\text{C}$ for 72 h. After cooling to room temperature, the separated precipitate was washed for 5 times with tetrahydrofuran, and dried in vacuum at $180 \text{ }^\circ\text{C}$ for 24 h to obtain the dark red product. Subsequently, SH-COF powder was dispersed in IPA solution and stirred overnight to obtain relevant suspension for subsequent experiments.

Device fabrication

The pre-patterned indium tin oxide (ITO) substrates were sequentially ultrasonically washed with detergent, deionized water, acetone and isopropanol for 15 min. The processed substrates were further cleaned with O_3 /ultraviolet treatments for

15 min and finally transferred to a N₂-filled glovebox before used. For the hole-transporting layer, MeO-2PACz solution (0.5 mg ml⁻¹ in ethyl alcohol) was spin-coated on the ITO substrate at 3000 rpm for 30 s, and then annealed at 100 °C for 10 min. The Perovskite precursor solution (FA_{0.95}Cs_{0.05}PbI₃) was obtained by mixing FAI, PbI₂, and CsI in DMF: DMSO mixed solvent (volume ratio: 4 to 1). The perovskite films were deposited on the above substrates by a two-step spin-coating process, 2000 rpm for 10 s and 4000 rpm for 30s, respectively. 150 μL CB as anti-solvent was poured on the spinning film at 35 s and then annealed at 100 °C for 30 min. Then, PC₆₁BM (20 mg mL⁻¹ in CB) and BCP (0.5 mg mL⁻¹ in IPA) solutions were spin-coated onto the substrates at 3000 rpm for 40 s and 6000 rpm for 30 s, respectively. Next, 30 μL of SH-COF suspension (0, 1, 2, 3 and 5 mg mL⁻¹ in IPA) was deposited on the above films at 4000 rpm for 30 s. Finally, a 90 nm Ag electrode was obtained by means of thermal evaporation under high-vacuum (less than 2.8 × 10⁻⁴ Pa).

Characterization

The X-ray diffraction (XRD) curves were measured on a Bruker Discovery D8 diffractometer with Cu-Kα radiation ($\lambda=1.54 \text{ \AA}$) at 40 kV. Fourier transform infrared (FTIR) spectra were characterized on a Thermo Scientific Nicolet iS50 instrument. X-ray photoelectron spectroscopy (XPS) and ultraviolet photoelectron spectroscopy (UPS) were carried out on the Thermo Scientific Escalab 250Xi instrument equipped with Mg-Kα source. The morphological properties of the perovskite films were identified via a field emission scanning electron microscopy (SEM, Hitachi S4700). The atomic force microscope (AFM) was investigated on the Multimode 8 AFM from Bruker. UV-Vis absorption spectra of the perovskite films were obtained on an ocean optics spectrum testing system with DH-2000-BAL UV-VIS-NIR light source. Steady-state photoluminescence (PL) spectra were measured by performing a Laser405-1HS illuminant. Time-resolved PL (TRPL) measurements were performed using a FLS920 from Edinburgh Instruments Ltd./UK. The current density-voltage (J - V) measurements and space-charge-limited current (SCLC) performance were executed through a Keithley 2400 source meter equipped with a xenon lamp-based solar simulator (AM 1.5G, irradiance of 100 mW·cm⁻²). The external quantum efficiency (EQE) was

recorded with AC mode on an SRF50 system. The electrochemical impedance spectra (EIS) were measured using a Zennium-IM6 electrochemical workstation under dark conditions.

Theoretical calculation details

We have used the first-principles Vienna Ab Initio Package (VASP) to complete all calculations. The exchange correlation functional is described by the Perdue-Burke-Ernzerhof (PBE) method in the generalized gradient approximation (GGA) with the plane wave cut-off energy of 450 eV. For the optimization process, the electron energy is self-consistent when it is converged to the accuracy of 1×10^{-5} eV, and the convergence criteria for atomic forces are set at less than 0.03 eV/Å. The Brillouin zone is divided by the number of K-point grids centered on the Γ point. While $1 \times 2 \times 1$ grid of K-points is used for electronic states analysis. The DFT-D3 method of Grimme is enabled to describe the dispersion interactions. The differential charge density between SH-COF molecules and Ag is defined as $\Delta \rho$, $\Delta \rho = \rho_{AB} - \rho_A - \rho_B$, where ρ_{AB} represents the structure charge density after interface optimization, ρ_A represented the charge density of SH-COF, ρ_B represented the charge density of Ag. The adsorption energy (E_{ads}) of SH-COF molecules on the Ag surface is defined as E_{ads} , $E_{ads} = E_{A+B} - E_A - E_B$, where E_{A+B} , E_A , E_B were the total energy of SH-COF molecules are adsorbed on the Ag surface, the energy of SH-COF molecules, the energy of the Ag film, respectively.

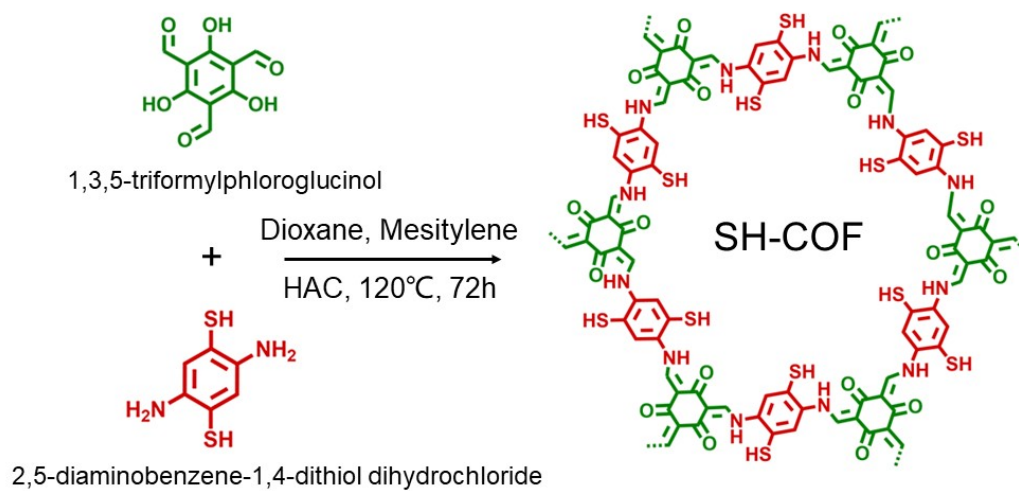


Figure S1. The synthesis scheme of SH-COF.

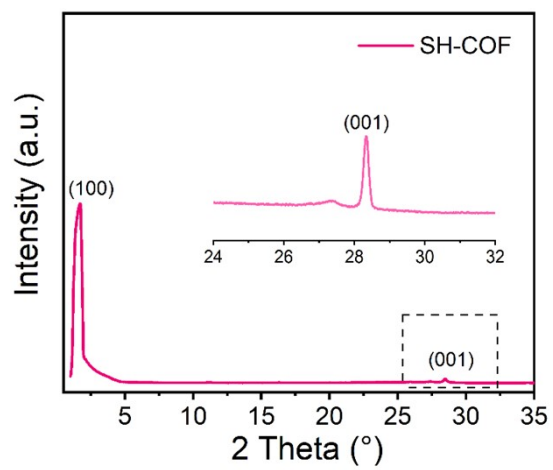


Figure S2. The XRD pattern of SH-COF.

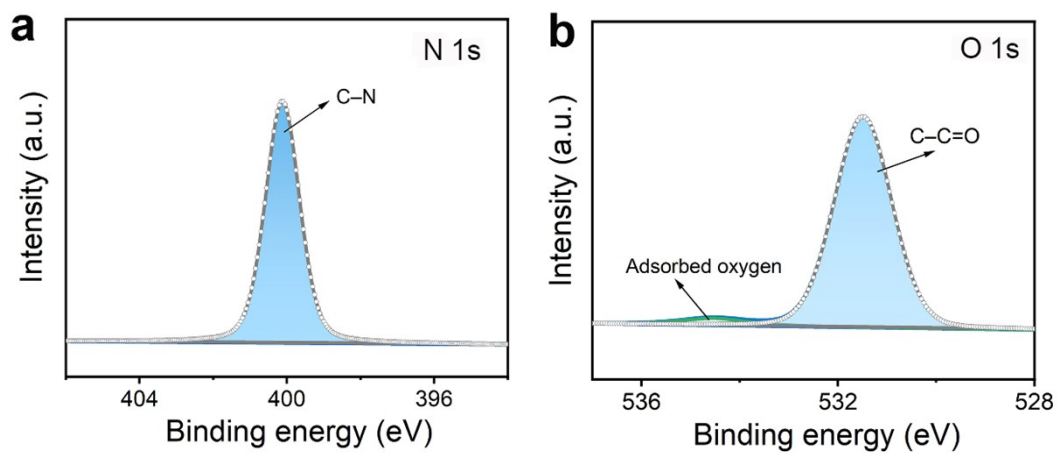


Figure S3. XPS pattern of **a)** N 1s and **b)** O 1s peaks of SH-COF.

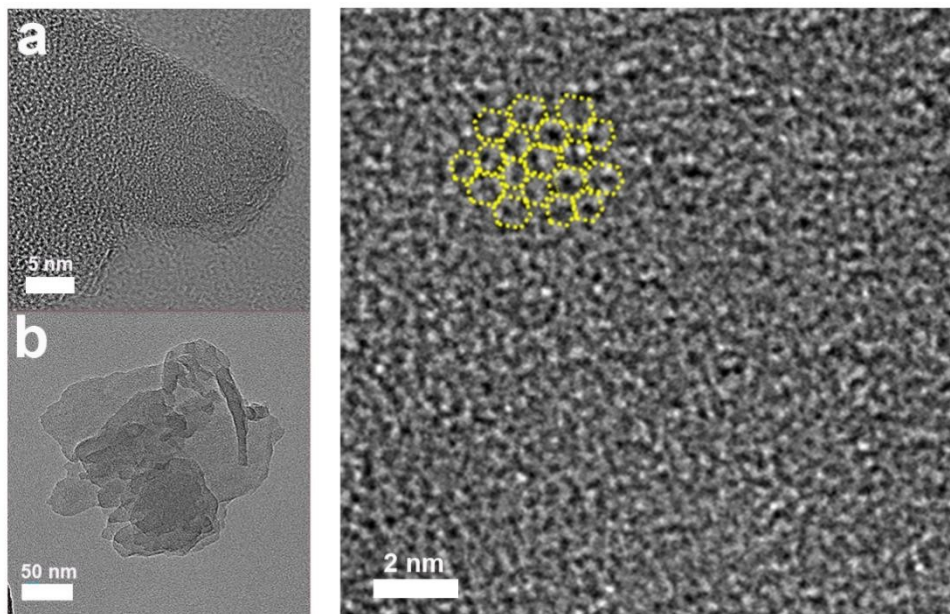


Figure S4. High-resolution transmission electron microscopy (TEM) image of SH-COF.

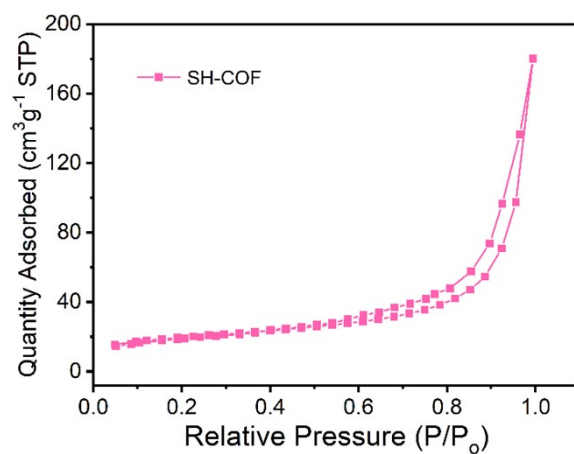


Figure S5. N₂ adsorption/desorption isotherms of SH-COF.

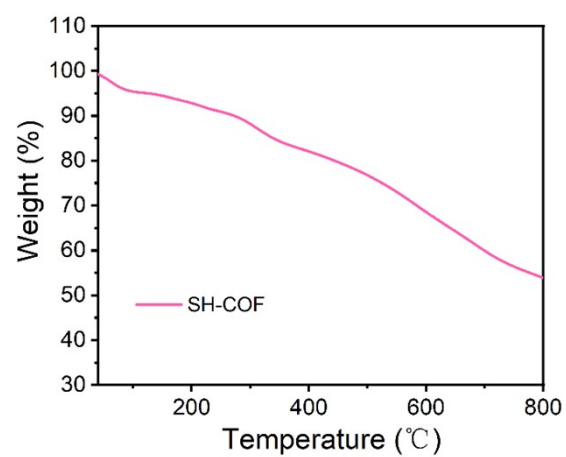


Figure S6. The weight and temperature dependence of SH-COF.

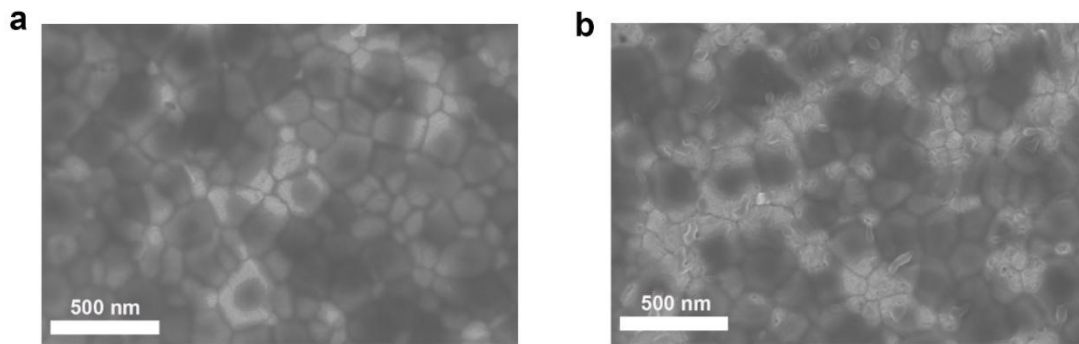


Figure S7. Top-view SEM images of **a)** perovskite/PCBM and **b)** perovskite/PCBM/SH-COF films.

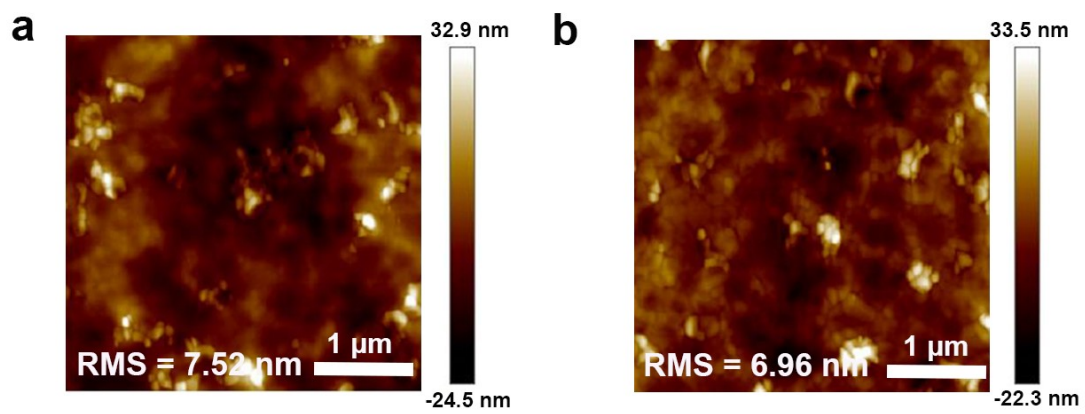


Figure S8. AFM images of **a)** perovskite/PCBM and **b)** perovskite/PCBM/SH-COF films.

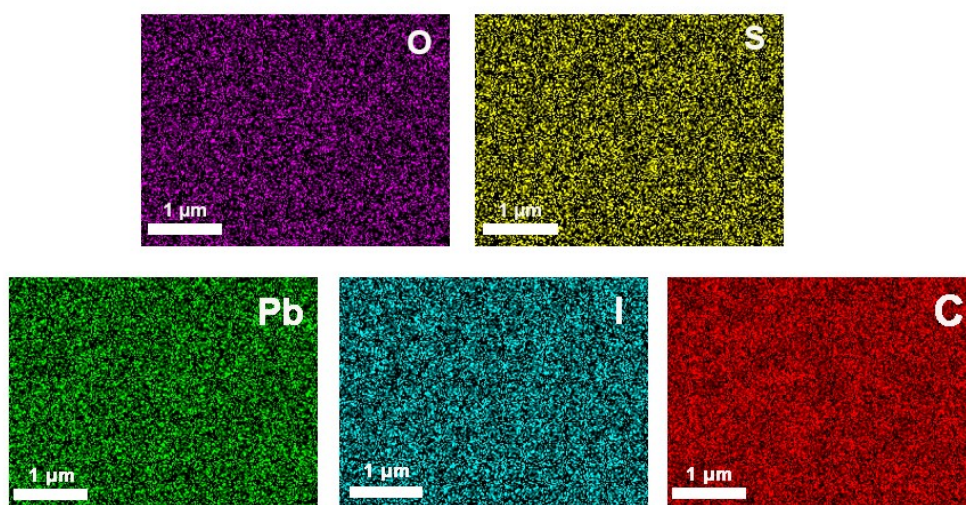


Figure S9. EDS mapping of C, Pb, I, S, O elements of the perovskite/PCBM/SH-COF film.

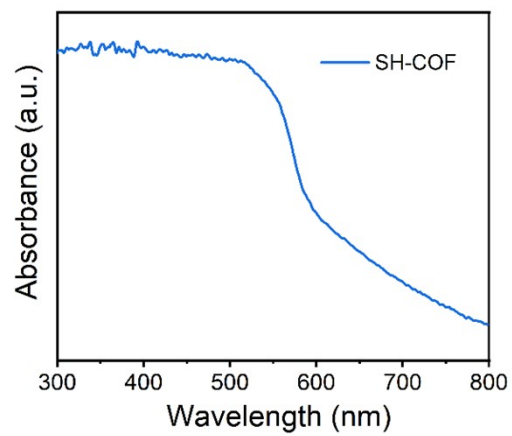


Figure S10. UV-vis diffuse reflectance spectrum of SH-COF.

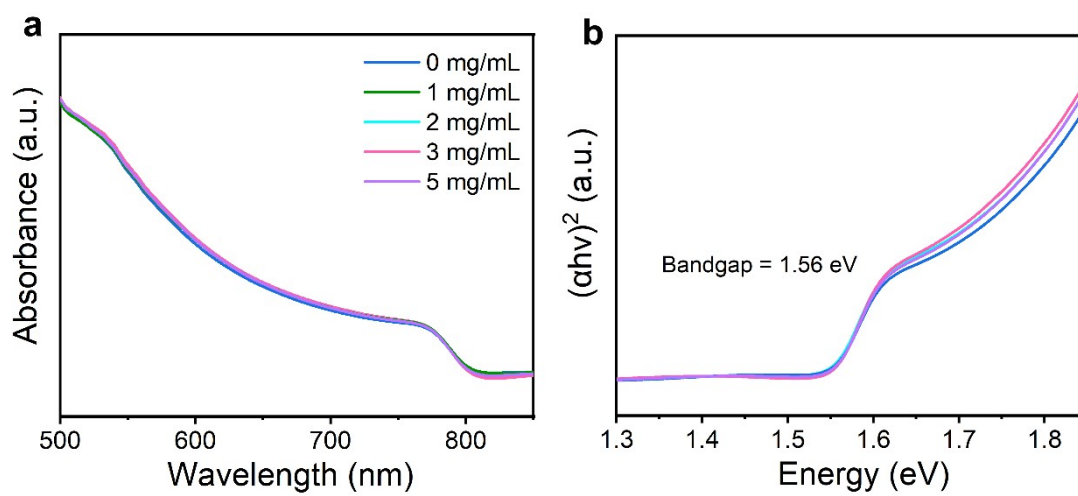


Figure S11. a) UV-vis spectra of perovskite/PCBM/SH-COF films with different concentrations of SH-COF, and b) the Tauc plot of the perovskite film.

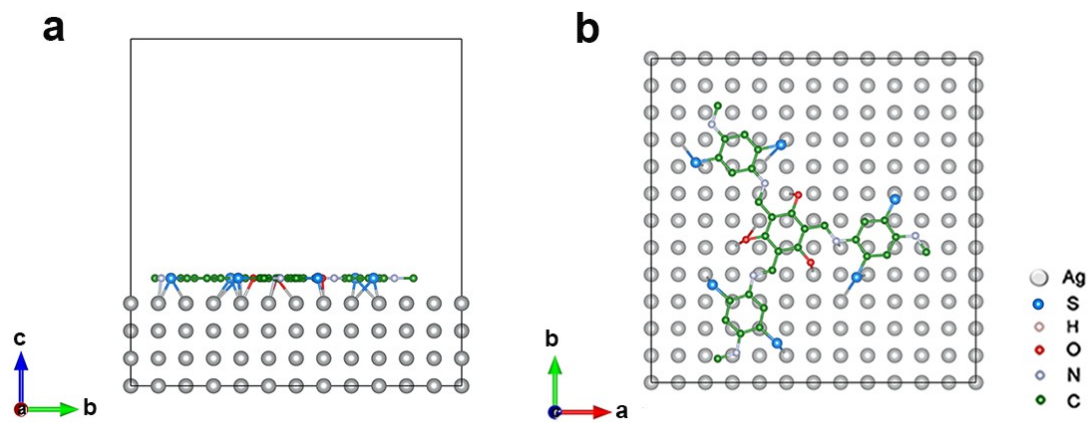


Figure S12. The theoretical model of SH-COF molecule and Ag before optimization: **a)** front view and **b)** top view.

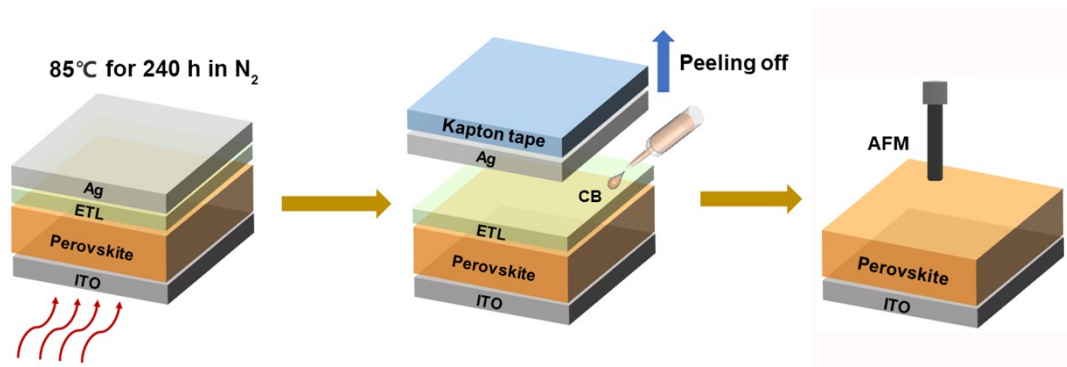


Figure S13. The preparation process of perovskite films from the aging devices for AFM characterizations, the corresponding device structure is ITO/perovskite/PCBM/BSP/SH-COF/Ag.

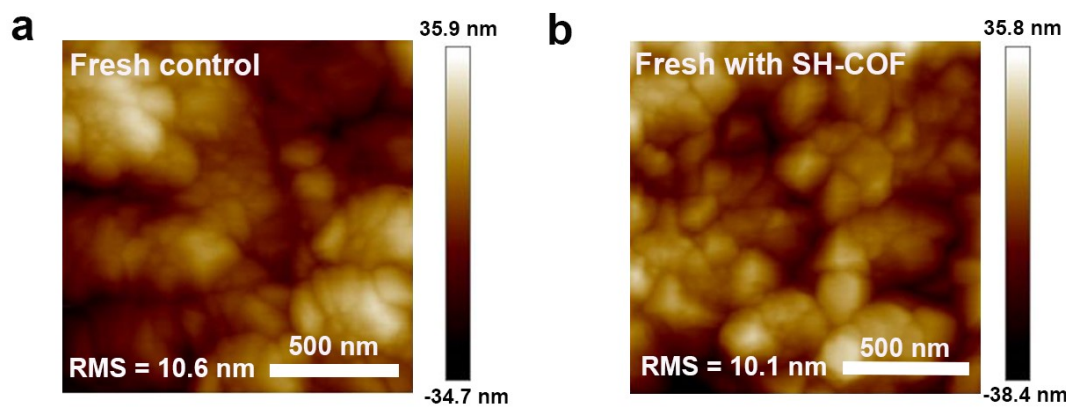


Figure S14. AFM images of perovskite films from the devices **d)** without and **e)** with SH-COF before thermal aging.

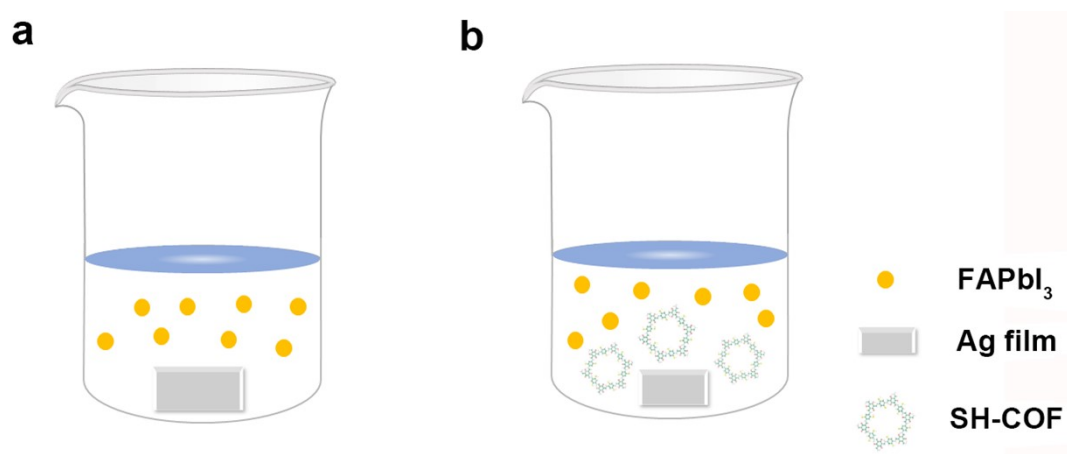


Figure S15. Schematic diagram of immersing experiments. The Ag/ITO films are immersed in FAPbI₃ dispersion (15 mg mL⁻¹ in isopropanol) without or with SH-COF (5.0 mg mL⁻¹).

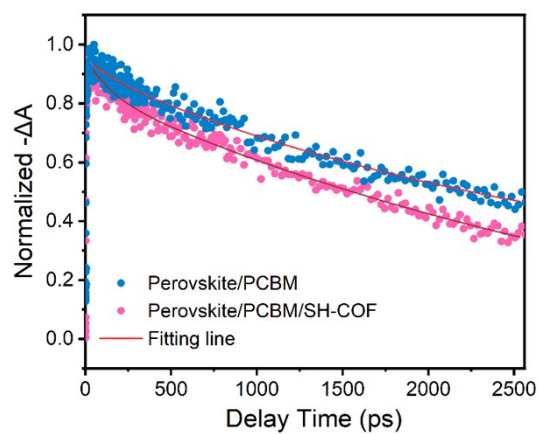


Figure S16. TA spectra as a function of delay time for perovskite/PCBM and perovskite/PCBM/SH-COF films.

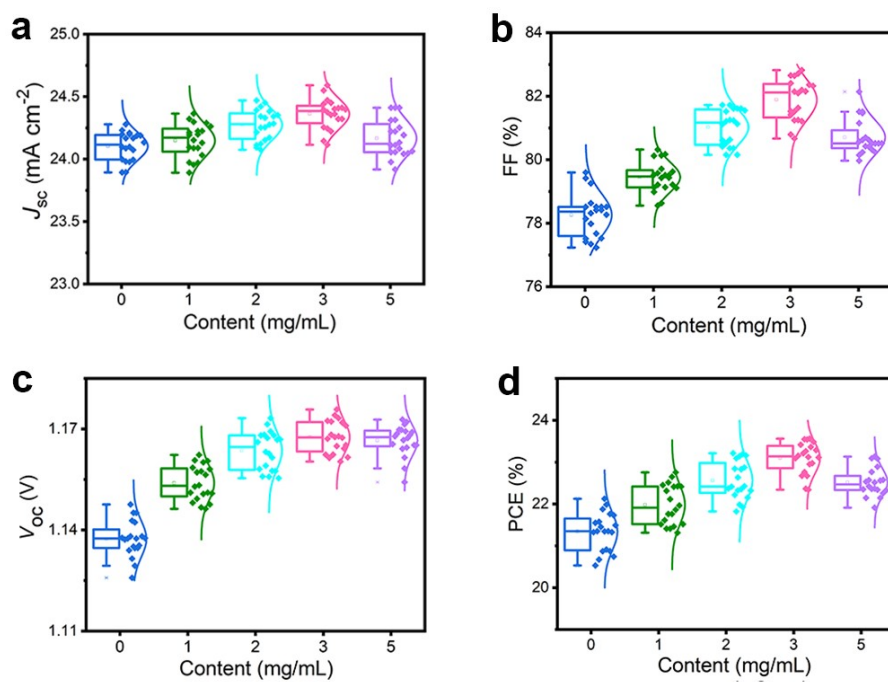


Figure S17. Statistical distribution of the devices with different concentrations of SH-COF of

a) J_{sc} , b) FF, c) V_{oc} , and d) PCE.

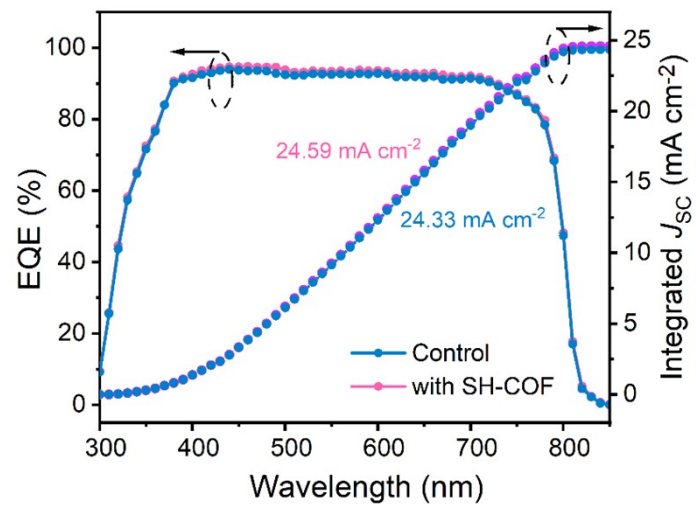


Figure S18. EQE curves of the control and SH-COF modified devices.

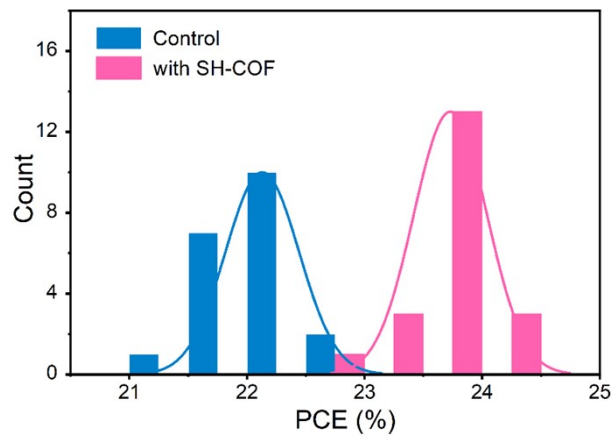


Figure S19. Statistics of PCE distribution of the devices with and without SH-COF layer (20 devices).

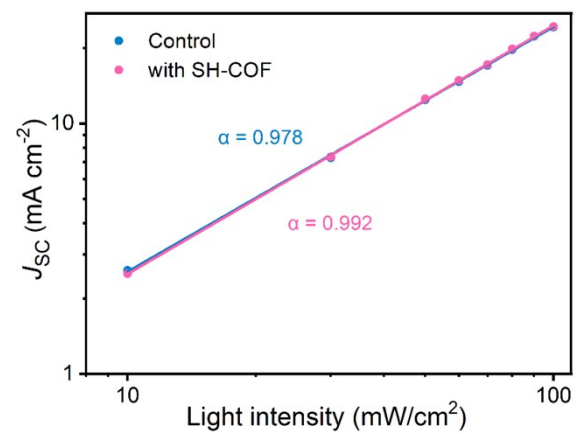


Figure S20. J_{sc} versus light intensity plots of the control and SH-COF modified devices.

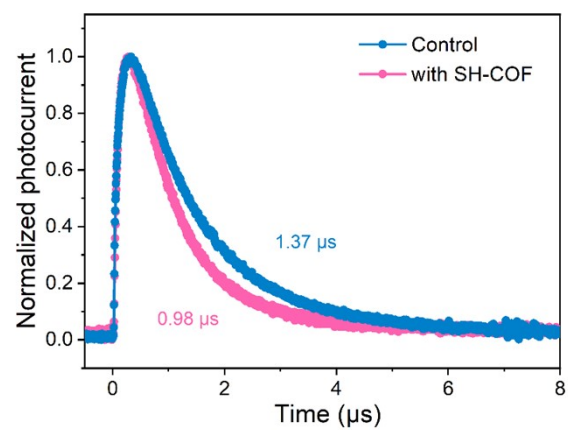


Figure S21. TPC curves of the control and SH-COF modified devices.

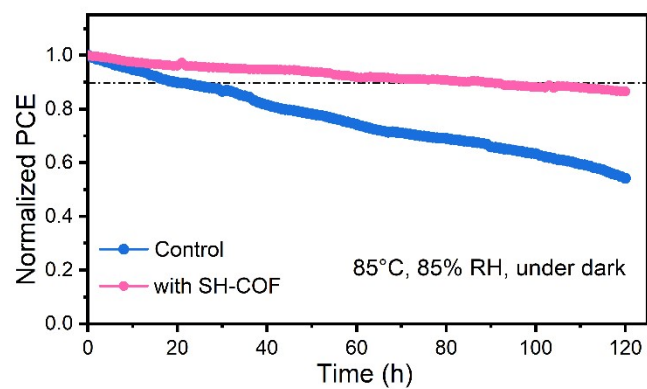


Figure S22. The long-term operational stability of the unencapsulated devices during 85°C and 85% RH aging.

Table S1. Summary of fitting parameters of time-resolved PL (TRPL) spectra.

Sample	A_1	τ_1 (ns)	A_2	τ_2 (ns)	τ_{ave} (ns)
Perovskite	4634.5	68.94	5235	5.59	63.59
Perovskite/SH-COF	2116.1	26.73	7982	3.74	18.79
Perovskite/PCBM	2850.7	19.01	6931	3.51	14.21
Perovskite/PCBM/SH-COF	942.1	18.03	7970	2.32	9.84

The average carrier lifetime (τ_{ave}) is obtained by the following formula: $\tau_{ave} = (A_1\tau_1 + A_2\tau_2)/(A_1 + A_2)$, where A_1 and A_2 are the fitting amplitudes.

Table S2. The average J - V performance of the devices with different concentrations of SH-COF.

(The values are obtained from 20 devices)

SH-COF (mg mL⁻¹)	J_{sc} (mA cm⁻²)	V_{oc} (V)	FF (%)	PCE (%)
0	24.10±0.11	1.14±0.005	78.25±0.66	21.34±0.43
1	24.15±0.13	1.15±0.005	79.45±0.47	21.98±0.46
2	24.27±0.12	1.16±0.006	81.03±0.55	22.56±0.44
3	24.36±0.12	1.17±0.004	81.89±0.64	23.10±0.36
5	24.17±0.14	1.16±0.004	80.71±0.54	22.52±0.32

Table S3. Solar cell performance parameters of the champion devices with and without SH-COF.

Sample	J_{sc} (mA cm⁻²)	V_{oc} (V)	FF (%)	PCE (%)
Control	24.61	1.134	79.73	22.25
Control	24.79	1.142	80.15	22.69
with SH-COF	24.98	1.172	82.14	24.05
with SH-COF	25.02	1.173	82.18	24.12

Table S4. Comparison of PCE and thermal stability of PSCs with different barrier materials.

Device structure	Barrier	PCE	Thermal stability test	% of PCE is maintained	Year
FTO/PEDOT:PSS/MAPbI ₃ /PCBM/AZO/SnO _x /Ag	AZO/SnO _x	12.8%	Dark, 60°C in N ₂ , 1032 h	100%	2017 ^[1]
FTO/NiMgLiO/MAPbI ₃ /PCBM/CeO _x /Ag	CeO _x	18.69%	MPP condition in air, 200 h	91%	2018 ^[2]
FTO/NiMgLiO/FAMACsPbI ₃ /PCBM/BCP/Bi/Ag	Bi	18.67%	Dark, 85°C in N ₂ , 500 h	85.2%	2019 ^[3]
ITO/NiO _x /FA _{0.85} MA _{0.15} Pb(I _{0.75} Br _{0.25}) ₃ /PCBM-C ₃ N ₄ /BCP/Ag	C ₃ N ₄	15.6% (36 cm ²)	Dark, 85°C in N ₂ , 1000 h	95%	2019 ^[4]
ITO/P3CT/MAPbI ₃ /PCBM/C ₆₀ /TPBi/BTA/Cu	BTA	19.56%	Dark, 85 °C in N ₂ , 1100 h	90.7%	2020 ^[5]
ITO/PTAA/CsFAMAPbI ₃ /PCBM/CIL/Au	CIL	20%	MPP condition in N ₂ , 250 h	80%	2021 ^[6]
ITO/NiO _x /CsFAMAPbI ₃ /PCBM/BCP:TTTS/Ag	TTTS	22.59%	Dark, 85°C in N ₂ , 1500 h	93%	2022 ^[7]
ITO/PTAA/MAPbI ₃ /PCBM/OXD-7/Ag	OXD-7	21.83%	Dark, 85°C in N ₂ , 1080 h	80%	2023 ^[8]
ITO/PTAA/FA _{0.95} Cs _{0.05} PbI ₃ /C ₆₀ /ALD-SnO ₂ /amp-ZrN _x /Cu	amp-ZrN _x	23.1%	Dark, 85°C in N ₂ , 1100 h	90%	2023 ^[9]
FTO/MeO-2PACz/RbCsMAFAPb(I _{0.95} Br _{0.05}) ₃ /PCBM/YbO _x /Cu	YbO _x	25.2%	Dark, 85°C in N ₂ , 500 h	98%	2024 ^[10]
ITO/MeO-2PACz/FA _{0.95} Cs _{0.05} PbI ₃ /PCBM/BCP/SH-COF/Ag	SH-COF	24.12%	Dark, 85°C in N ₂ , 1200 h	93.3%	This work

Table S5. Solar cell performance parameters of the champion devices with and without SH-COF for the area of 1.0 cm².

Sample	<i>J</i>_{sc} (mA cm⁻²)	<i>V</i>_{oc} (V)	FF (%)	PCE (%)
Control	23.83	1.11	75.95	20.09
with SH-COF	24.12	1.15	77.98	21.63

Table S6. EIS fitting parameters of the control and SH-COF modified devices.

Sample	R_s (Ohm)	R_{rec} (Ohm)	C_{rec} (F)
Control	147.6	12368	3.45×10^{-8}
with SH-COF	137.1	25958	2.43×10^{-8}

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